

AMENDMENTS TO THE CLAIMS

1. (Currently Amended) A method of modifying conductive wiring, comprising:

providing a semiconductor substrate;

forming a first barrier on the semiconductor substrate;

forming a conductive wiring on the first barrier;

performing a thermal treatment on the semiconductor substrate;

and

forming a second barrier on the conductive wiring; ~~and after~~
performing the thermal treatment.

~~performing a thermal treatment on the semiconductor substrate.~~

2. (Original) The method as claimed in claim 1, wherein the first barrier and the second barrier individually comprises a stacked Ti/TiN.

3. (Original) The method as claimed in claim 1, wherein the conductive wiring comprises a Cu/Al alloy or a Cu/Al/Si alloy.

4. (Original) The method as claimed in claim 1, wherein the thermal treatment is performed by baking.

5 . (Original) The method as claimed in claim 1, wherein the thermal treatment is performed by quenching.

6-7. (Cancelled)

8. (Original) The method as claimed in claim 1, wherein the thermal treatment is performed in an atmosphere containing nitrogen.

9. (Cancelled)

10. (Original) The method as claimed in claim 1, wherein the thermal treatment is performed at a temperature of about 200~400°C.

11. (Original) The method as claimed in claim 5, wherein the substrate is quenched from a high temperature range of about 350°C to a low temperature range of about 23°C in a short interval between about 50 to 70 seconds.

12. (Currently Amended) A method of modifying conductive wiring, comprising:

providing a semiconductor substrate;

forming a first barrier on the semiconductor substrate;

forming a conductive wiring on the first barrier;

~~forming a second barrier on the conductive wiring; and~~

treating the semiconductor substrate with a nitrogen-containing gas[.]; and

forming a second barrier on the conductive wiring; and after treating the semiconductor substrate with the nitrogen-containing gas.

13. (Original) The method as claimed in claim 12, wherein the first barrier and the second barrier individually comprise a stacked Ti/TiN.

14. (Original) The method as claimed in claim 12, wherein the conductive wiring comprises a Cu/Al alloy or a Cu/Al/Si alloy.

15-17. (Cancelled)

18. (Original) The method as claimed in claim 12, wherein the nitrogen-containing gas comprises N₂O or N₂.

19-20. (Cancelled)

AMENDMENTS TO THE DRAWINGS

Attached hereto is one (1) sheet of corrected formal drawings that comply with the provisions of 37 C.F.R. § 1.84. The corrected formal drawings incorporate the following drawing changes:

In Fig. 3, the notation "S104" has been omitted.

It is respectfully requested that the corrected formal drawings be approved and made a part of the record of the above-identified application.